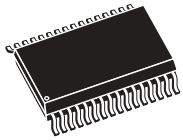
M68AW127B

1Mbit (128K x8), 3.0V Asynchronous SRAM

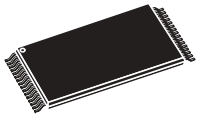
FEATURES SUMMARY

- SUPPLY VOLTAGE: 2.7 to 3.6V
- 128K x 8 bits SRAM with OUTPUT ENABLE
- EQUAL CYCLE and ACCESS TIMES: 70ns
- LOW STANDBY CURRENT
- LOW V_{CC} DATA RETENTION: 1.5V
- TRI-STATE COMMON I/O
- LOW ACTIVE and STANDBY POWER

Figure 1. Packages



SO32 (MC)



TSOP32
8 x 20mm
(N)

TSOP32
8 x 13.4mm
(NK)

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SUMMARY DESCRIPTION

The M68AW127B is a 1Mbit (1,048,576 bit) CMOS SRAM, organized as 131,072 words by 8 bits. The device features fully static operation requiring no external clocks or timing strobes, with equal address access and cycle times. It requires a single 2.7 to 3.6V supply.

This device has an automatic power-down feature, reducing the power consumption by over 99% when deselected.

The M68AW127B is available in SO32, TSOP32 8x20mm and TSOP32 8x13.4mm packages.

Figure 2. Logic Diagram

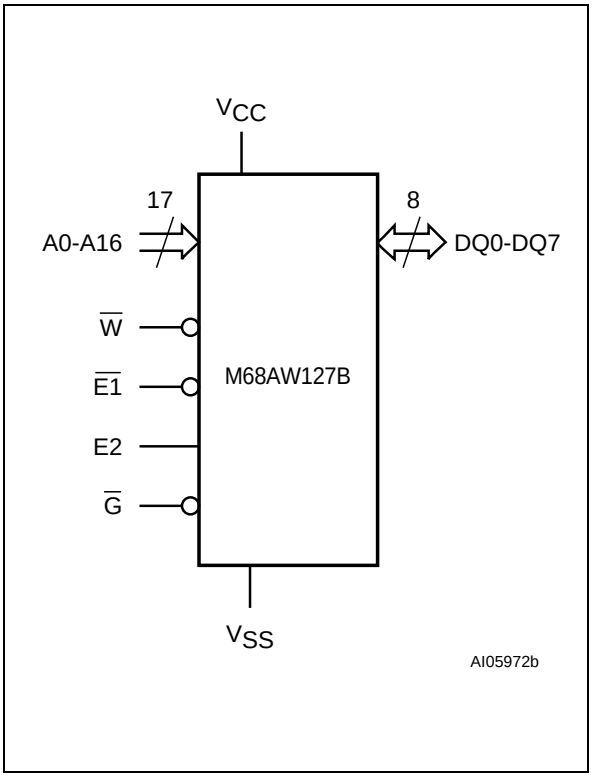


Table 1. Signal Names

A0-A16	Address Inputs
DQ0-DQ7	Data Input/Output
$\overline{E1}$	Chip Enable
E2	Chip Enable
$\overline{G}$	Output Enable
$\overline{W}$	Write Enable
V_{CC}	Supply Voltage
V_{SS}	Ground

Figure 3. SO Connections

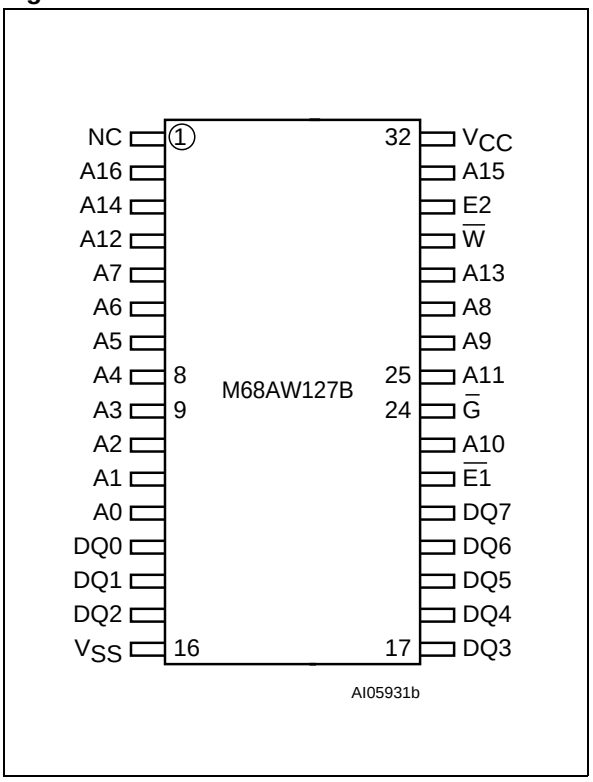


Figure 4. TSOP Connections

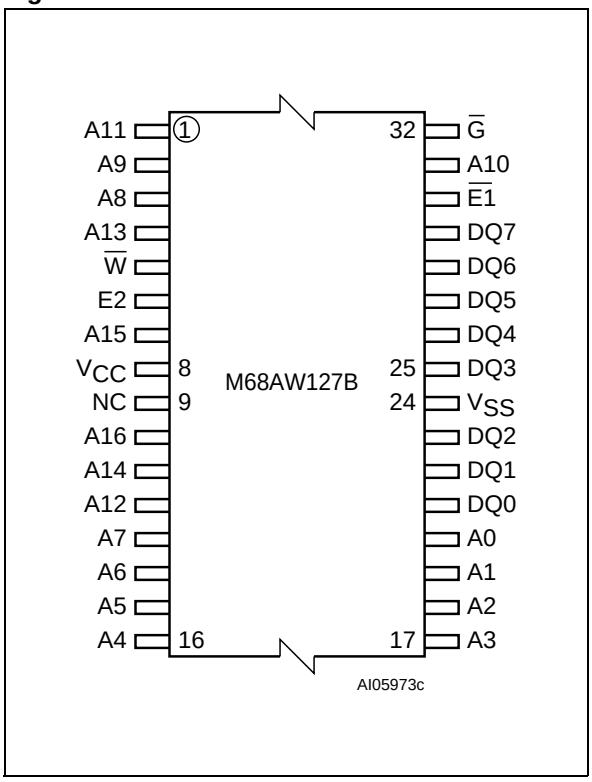
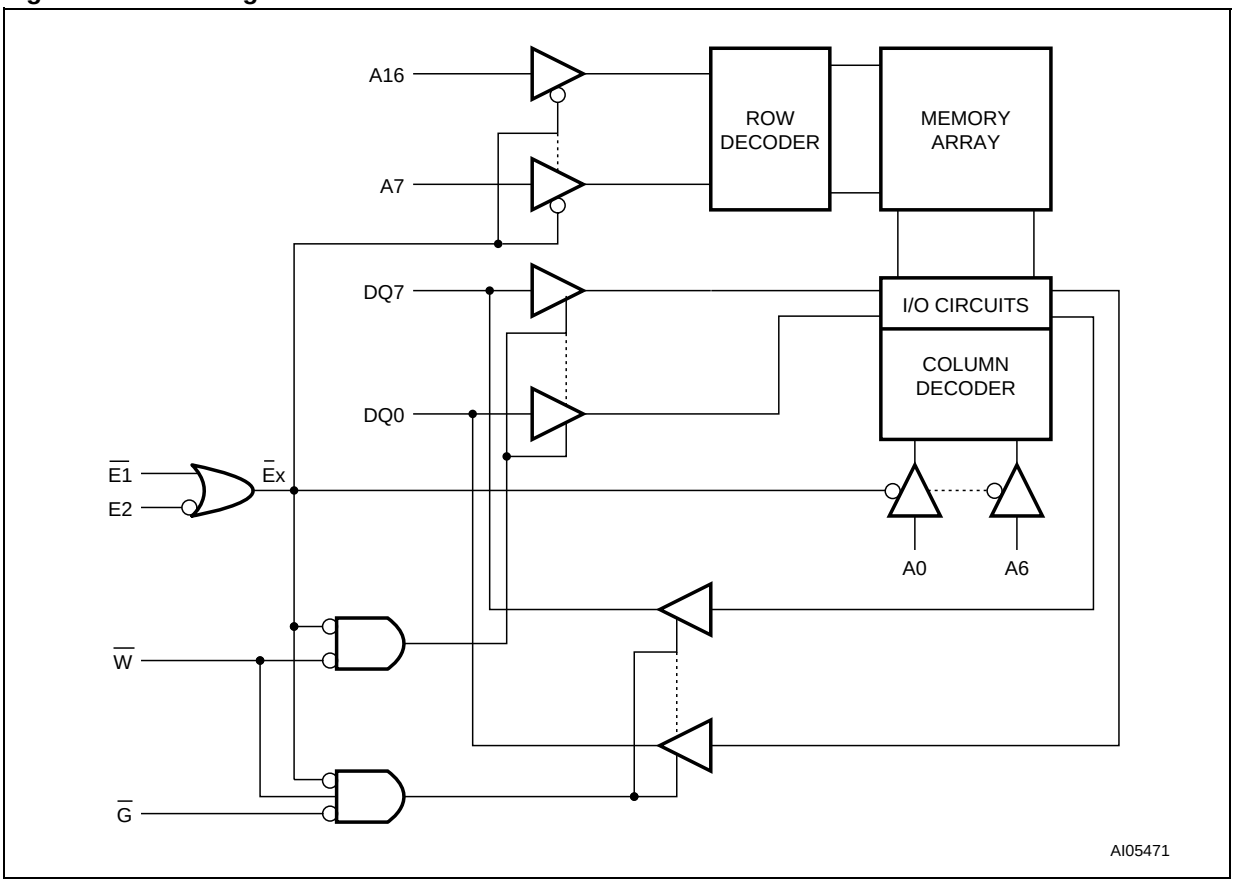


Figure 5. Block Diagram



OPERATION

The M68AW127B has a Chip Enable power down feature which invokes an automatic standby mode whenever Chip Enable is de-asserted ($\overline{E1}$ = High), or Chip Select is asserted (E2 = Low). An Output Enable ($\overline{G}$) signal provides a high-speed, tri-state control, allowing fast read/write cycles to be achieved with the common I/O data bus. Operational modes are determined by device control inputs $\overline{W}$ and $\overline{E1}$ as summarized in the Operating Modes table (Table 2).

Read Mode

The M68AW127B is in the Read mode whenever Write Enable ($\overline{W}$) is High with Output Enable ($\overline{G}$) Low, Chip Enable ($\overline{E1}$) is asserted and Chip Select (E2) is de-asserted. This provides access to data from eight of the 1,048,576 locations in the static memory array, specified by the 17 address inputs. Valid data will be available at the eight output pins within t_{AVQV} after the last stable address, providing $\overline{G}$ is Low and $\overline{E1}$ is Low. If Chip Enable or Output Enable access times are not met, data access will be measured from the limiting parameter (t_{ELQV} or t_{GLQV}) rather than the address. Data out may be indeterminate at t_{ELQX} and t_{GLQX}, but data lines will always be valid at t_{AVQV}.

Write Mode

The M68AW127B is in the Write mode whenever the $\overline{W}$ and $\overline{E1}$ pins are Low and the E2 pin is High. Either the Chip Enable input ($\overline{E1}$) or the Write Enable input ($\overline{W}$) must be de-asserted during Address transitions for subsequent write cycles. Write begins with the concurrence of $\overline{E1}$ being active with $\overline{W}$ low. Therefore, address setup time is referenced to Write Enable and Chip Enable as t_{AVWL} and t_{AVEH}, respectively, and is determined by the latter occurring edge.

The Write cycle can be terminated by the earlier rising edge of $\overline{E1}$, or $\overline{W}$.

If the Output is enabled ($\overline{E1}$ = Low, E2 = High and $\overline{G}$ = Low), then $\overline{W}$ will return the outputs to high impedance within t_{WLQZ} of its falling edge. Care must be taken to avoid bus contention in this type of operation. Data input must be valid for t_{DVWH} before the rising edge of Write Enable, or for t_{DVEH} before the rising edge of $\overline{E1}$, whichever occurs first, and remain valid for t_{WHDX} or t_{EHDX}.

Table 2. Operating Modes

Operation	$\overline{E1}$	E2	$\overline{W}$	$\overline{G}$	DQ0-DQ7	Power
Read	V_{IL}	V_{IH}	V_{IH}	V_{IH}	Hi-Z	Active (I_{CC})
Read	V_{IL}	V_{IH}	V_{IH}	V_{IL}	Data Output	Active (I_{CC})
Write	V_{IL}	V_{IH}	V_{IL}	X	Data Input	Active (I_{CC})
Deselect	V_{IH}	X	X	X	Hi-Z	Standby (I_{SB})
Deselect	X	V_{IL}	X	X	Hi-Z	Standby (I_{SB})

X = V_{IH} or V_{IL}.

MAXIMUM RATING

Stressing the device above the rating listed in the "Absolute Maximum Ratings" table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the Operating sections of this specification is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability. Refer also to the STMicroelectronics SURE Program and other relevant quality documents.

Table 3. Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
I_O (1)	Output Current	20	mA
T_A	Ambient Operating Temperature	–55 to 125	°C
T_{STG}	Storage Temperature	–65 to 150	°C
V_{CC}	Supply Voltage	–0.3 to 4.6	V
V_{IO} (2)	Input or Output Voltage	–0.5 to V_{CC} +0.5	V
P_D	Power Dissipation	1	W

Note: 1. One output at a time, not to exceed 1 second duration.
2. Up to a maximum operating V_{CC} of 3.6V only.

DC AND AC PARAMETERS

This section summarizes the operating and measurement conditions, as well as the DC and AC characteristics of the device. The parameters in the following DC and AC Characteristic tables are derived from tests performed under the Measurement Conditions listed in the relevant tables. Designers should check that the operating conditions in their projects match the measurement conditions when using the quoted parameters.

Table 4. Operating and AC Measurement Conditions

Parameter		M68AW127B
V_{CC} Supply Voltage		2.7 to 3.6V
Ambient Operating Temperature	Range 1	0 to 70°C
	Range 6	–40 to 85°C
Load Capacitance (C_L)		100pF
Output Circuit Protection Resistance (R_1)		3.0kΩ
Load Resistance (R_2)		3.1kΩ
Input Rise and Fall Times		1ns/V
Input Pulse Voltages		0 to V_{CC}
Input and Output Timing Ref. Voltages		$V_{CC}/2$
Output Transition Timing Ref. Voltages		$V_{RL} = 0.3V_{CC}$; $V_{RH} = 0.7V_{CC}$

Figure 6. AC Measurement I/O Waveform

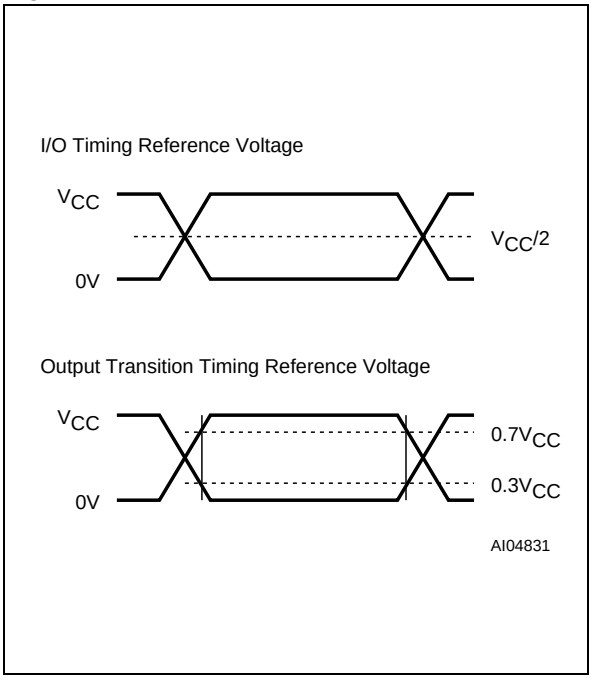


Figure 7. AC Measurement Load Circuit

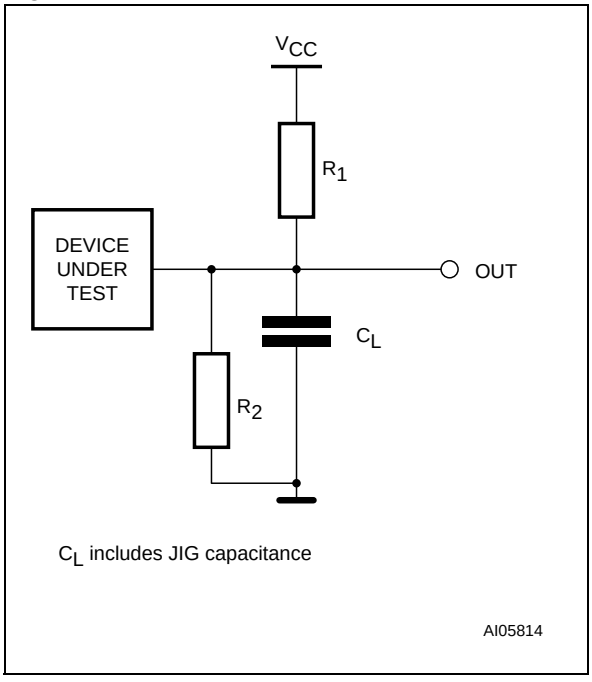


Table 5. Capacitance

Symbol	Parameter (1,2)	Test Condition	Min	Max	Unit
C_{IN}	Input Capacitance on all pins (except DQ)	V_{IN} = 0V		6	pF
C_{OUT}	Output Capacitance	V_{OUT} = 0V		8	pF

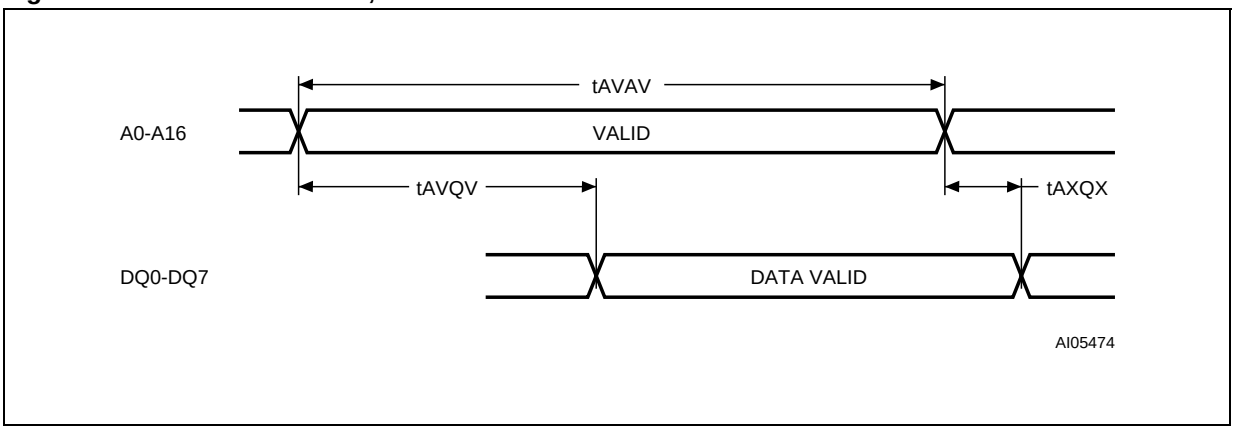
Note: 1. Sampled only, not 100% tested.
2. At T_A = 25°C, f = 1MHz, V_{CC} = 3.0V.

Table 6. DC Characteristics

Symbol	Parameter	Test Condition		Min	Typ	Max	Unit
I_{CC1} (1,2)	Supply Current	V_{CC} = 3.6V, f = $1/t_{AVAV}$, I_{OUT} = 0mA	70		6.0	15	mA
			100		25	35	mA
I_{CC2} (3)	Operating Supply Current	V_{CC} = 3.6V, f = 1MHz, I_{OUT} = 0mA	70			2	mA
	Operating Supply Current (READ)	V_{CC} = 3.6V, f = 1MHz, I_{OUT} = 0mA	100		1.5	5	mA
	Operating Supply Current (WRITE)				10	15	mA
I_{LI}	Input Leakage Current	0V ≤V_{IN} ≤V_{CC}		–1		1	µA
I_{LO} (4)	Output Leakage Current	0V ≤V_{OUT} ≤V_{CC}		–1		1	µA
I_{SB}	Standby Supply Current CMOS	V_{CC} = 3.6V, $\overline{E1}$ ≥ V_{CC} – 0.2V, E2 ≤0.2V, f = 0	70		2.5	15	µA
			100		0.3	10	µA
V_{IH}	Input High Voltage			2.2		V_{CC} + 0.3	V
V_{IL}	Input Low Voltage		70	–0.3		0.8	V
			100	–0.3		0.6	V
V_{OH}	Output High Voltage	I_{OH} = –1mA	70	2.4			V
			100	2.2			V
V_{OL}	Output Low Voltage	I_{OL} = 2.1mA				0.4	V

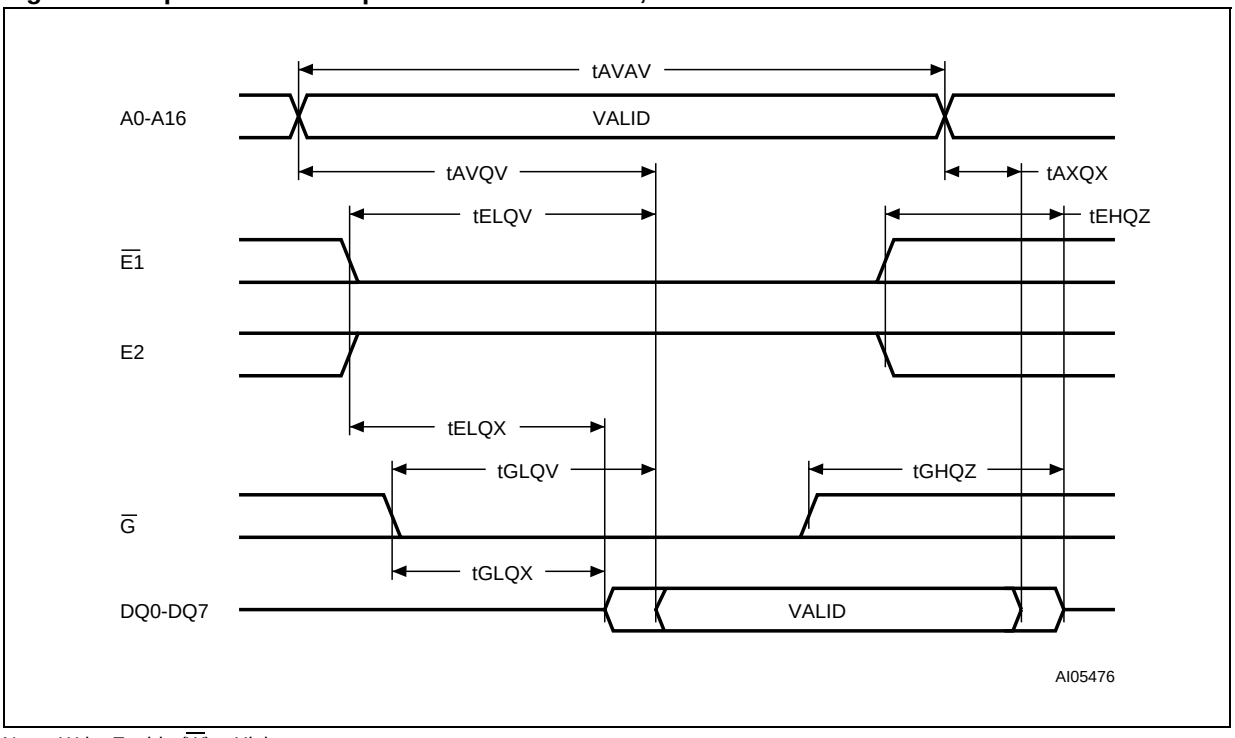
Note: 1. Average AC current, cycling at t_{AVAV} minimum.
2. $\overline{E1}$ = V_{IL}, E2 = V_{IH}, V_{IN} = V_{IH} or V_{IL}.
3. $\overline{E1}$ ≤0.2V or E2 ≥ V_{CC} –0.2V, V_{IN} ≤0.2V or V_{IN} ≥ V_{CC} –0.2V.
4. Output disabled.

Figure 8. Address Controlled, Read Mode AC Waveforms



Note: $\overline{E1}$ = Low, E2 = High, $\overline{G}$ = Low, $\overline{W}$ = High.

Figure 9. Chip Enable or Output Enable Controlled, Read Mode AC Waveforms.



Note: Write Enable ($\overline{W}$) = High.

Figure 10. Chip Enable Controlled, Standby Mode AC Waveforms

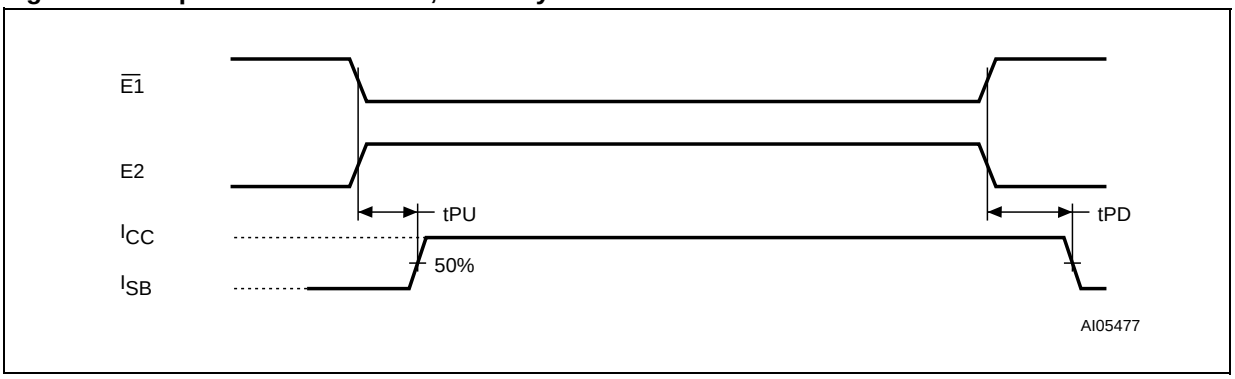


Table 7. Read and Standby Mode AC Characteristics

Symbol	Parameter		M68AW127B		Unit
			70	100	
t_{AVAV}	Read Cycle Time	Min	70	100	ns
t_{AVQV}	Address Valid to Output Valid	Max	70	100	ns
t_{AXQX} (1)	Data hold from address change	Min	5	15	ns
t_{EHQZ} (2,3)	Chip Enable High to Output Hi-Z	Max	25	30	ns
t_{ELQV}	Chip Enable Low to Output Valid	Max	70	100	ns
t_{ELQX} (1)	Chip Enable Low to Output Transition	Min	5	10	ns
t_{GHQZ} (2,3)	Output Enable High to Output Hi-Z	Max	25	30	ns
t_{GLQV}	Output Enable Low to Output Valid	Max	35	50	ns
t_{GLQX} (2)	Output Enable Low to Output Transition	Min	5	5	ns
t_{PD}	Chip Enable or $\overline{UB}$/$\overline{LB}$ High to Power Down	Max	55	70	ns
t_{PU}	Chip Enable or $\overline{UB}$/$\overline{LB}$ Low to Power Up	Min	0	0	ns

Note: 1. Test conditions assume transition timing reference level = $0.3V_{CC}$ or $0.7V_{CC}$.
2. At any given temperature and voltage condition, t_{GHQZ} is less than t_{GLQX} and t_{EHQZ} is less than t_{ELQX} for any given device.
3. These parameters are defined as the time at which the outputs achieve the open circuit conditions and are not referenced to output voltage levels.

Figure 11. Write Enable Controlled, Write AC Waveforms

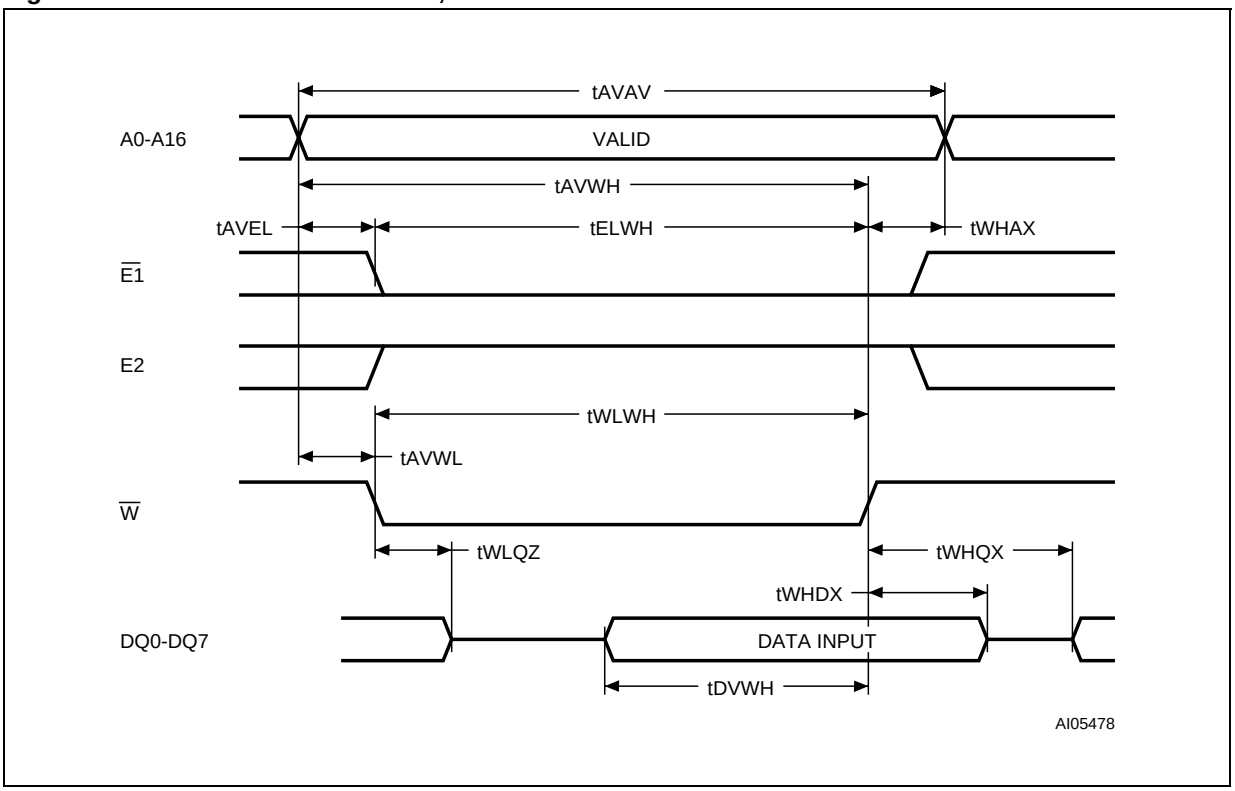


Figure 12. Chip Enable Controlled, Write AC Waveforms

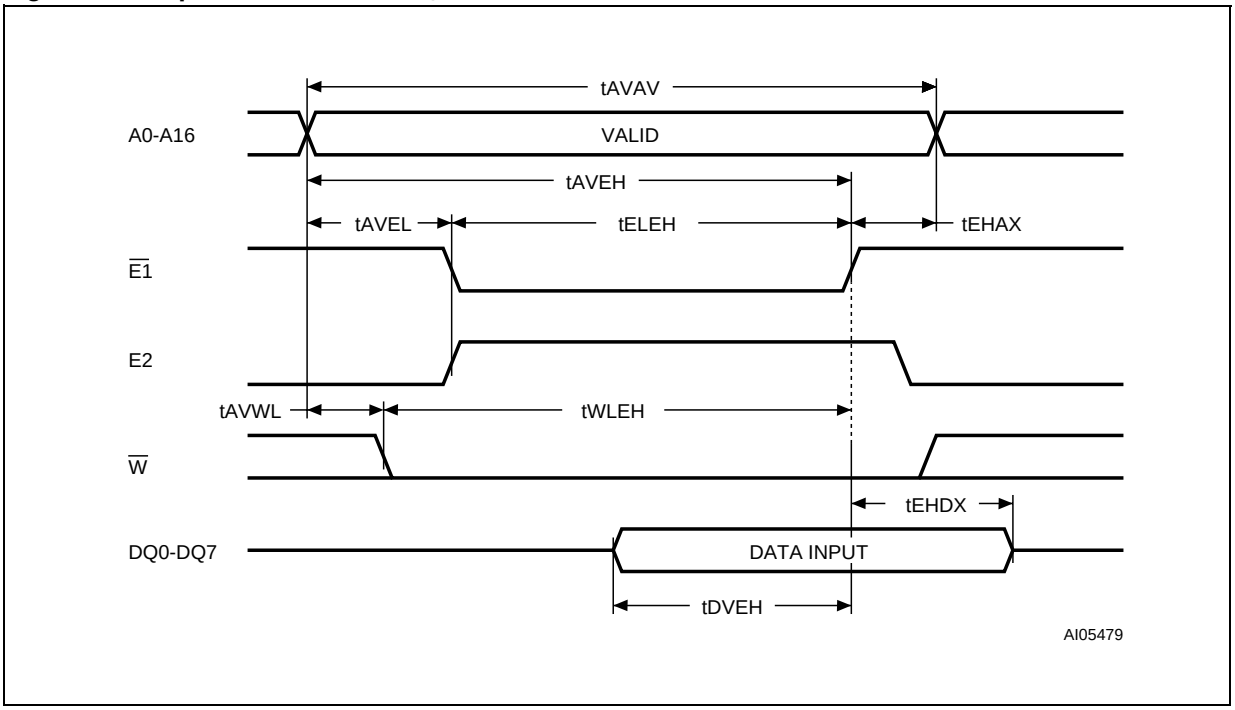
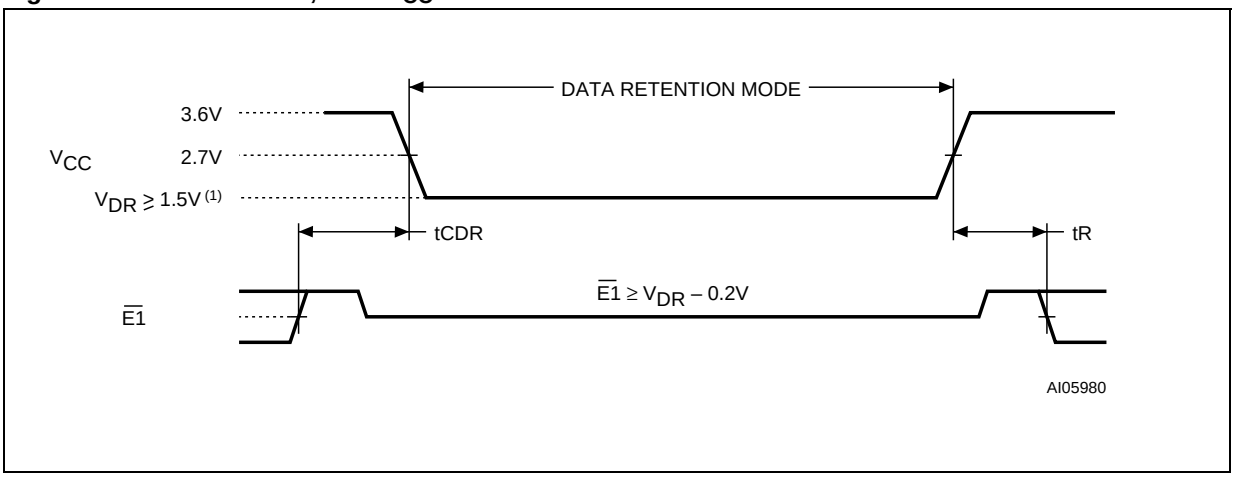


Table 8. Write Mode AC Characteristics

Symbol	Parameter		M68AW127B		Unit
			70	100	
t_{AVAV}	Write Cycle Time	Min	70	100	ns
t_{AVEH}	Address Valid to Chip Enable High	Min	60	80	ns
t_{AVEL}	Address valid to Chip Enable Low	Min	0	0	ns
t_{AVWH}	Address Valid to Write Enable High	Min	60	80	ns
t_{AVWL}	Address Valid to Write Enable Low	Min	0	0	ns
t_{DVEH}	Input Valid to Chip Enable High	Min	30	40	ns
t_{DVWH}	Input Valid to Write Enable High	Min	30	40	ns
t_{EHAX}	Chip Enable High to Address Transition	Min	0	0	ns
t_{EHDX}	Chip enable High to Input Transition	Min	0	0	ns
t_{ELEH}	Chip Enable Low to Chip Enable High	Min	60	80	ns
t_{ELWH}	Chip Enable Low to Write Enable High	Min	60	80	ns
t_{WHAX}	Write Enable High to Address Transition	Min	0	0	ns
t_{WHDX}	Write Enable High to Input Transition	Min	0	0	ns
t_{WHQX} (1)	Write Enable High to Output Transition	Min	5	5	ns
t_{WLEH}	Write Enable Low to Chip Enable High	Min	60	70	ns
t_{WLQZ} (1,2)	Write Enable Low to Output Hi-Z	Max	20	30	ns
t_{WLWH}	Write Enable Low to Write Enable High	Min	60	70	ns

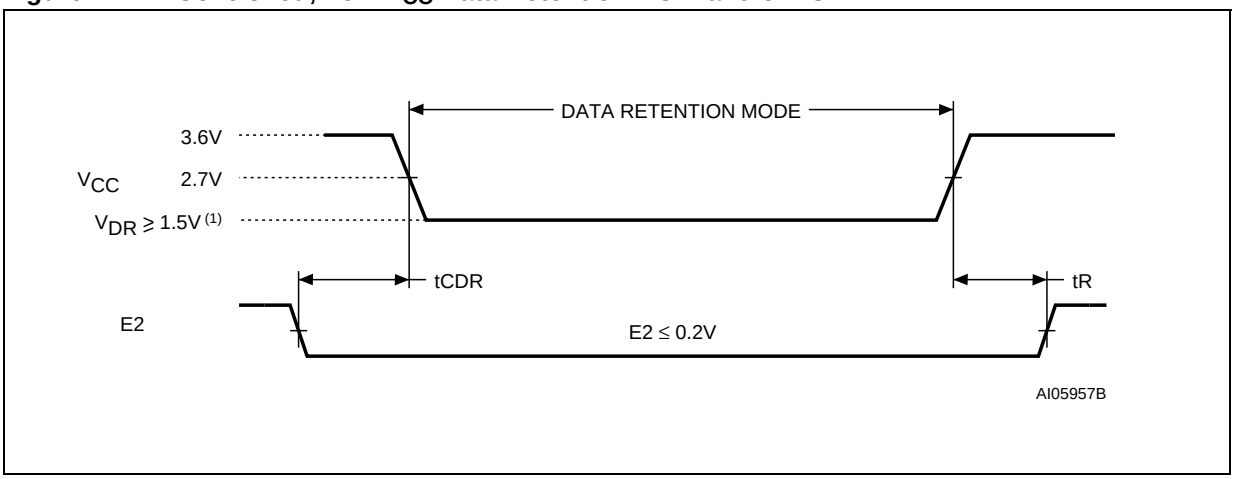
Note: 1. At any given temperature and voltage condition, t_{WLQZ} is less than t_{WHQX} for any given device.
2. These parameters are defined as the time at which the outputs achieve the open circuit conditions and are not referenced to output voltage levels.

Figure 13. $\overline{E1}$ Controlled, Low V_{CC} Data Retention AC Waveforms



Note: 1. For 100ns speed class $V_{DR} \geq 2.0V$.

Figure 14. E2 Controlled, Low V_{CC} Data Retention AC Waveforms



Note: 1. For 100ns speed class $V_{DR} \geq 2.0V$.

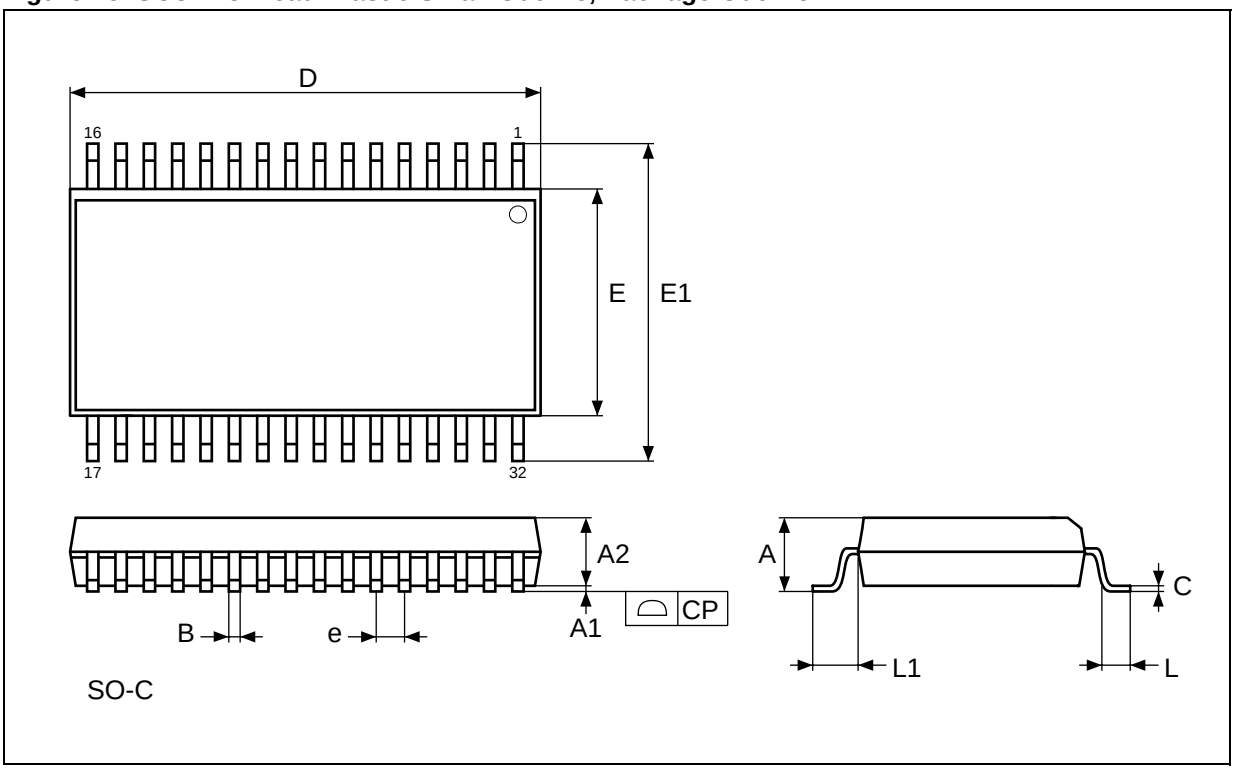
Table 9. Low V_{CC} Data Retention Characteristics

Symbol	Parameter	Test Condition		Min	Typ	Max	Unit
I_{CCDR} (1)	Supply Current (Data Retention)	V_{CC} = 1.5V, $\overline{E1} \geq V_{CC}$ –0.2V or E2 ≤0.2V, f = 0	70			4.5	µA
			100			5	µA
t_{CDR} (1,2)	Chip Deselected to Data Retention Time			0			ns
t_R (2)	Operation Recovery Time		70	t_{AVAV}			ns
			100	5			ms
V_{DR} (1)	Supply Voltage (Data Retention)	$\overline{E1} \geq V_{CC}$ –0.2V or E2 ≤0.2V, f = 0	70	1.5			V
			100	2.0			V

Note: 1. All other Inputs at $V_{IH} \geq V_{CC}$ –0.2V or $V_{IL} \leq$0.2V.
2. Tested initially and after any design or process that may affect these parameters. t_{AVAV} is Read cycle time.
3. No input may exceed V_{CC} +0.2V.

PACKAGE MECHANICAL

Figure 15. SO32 - 32 lead Plastic Small Outline, Package Outline

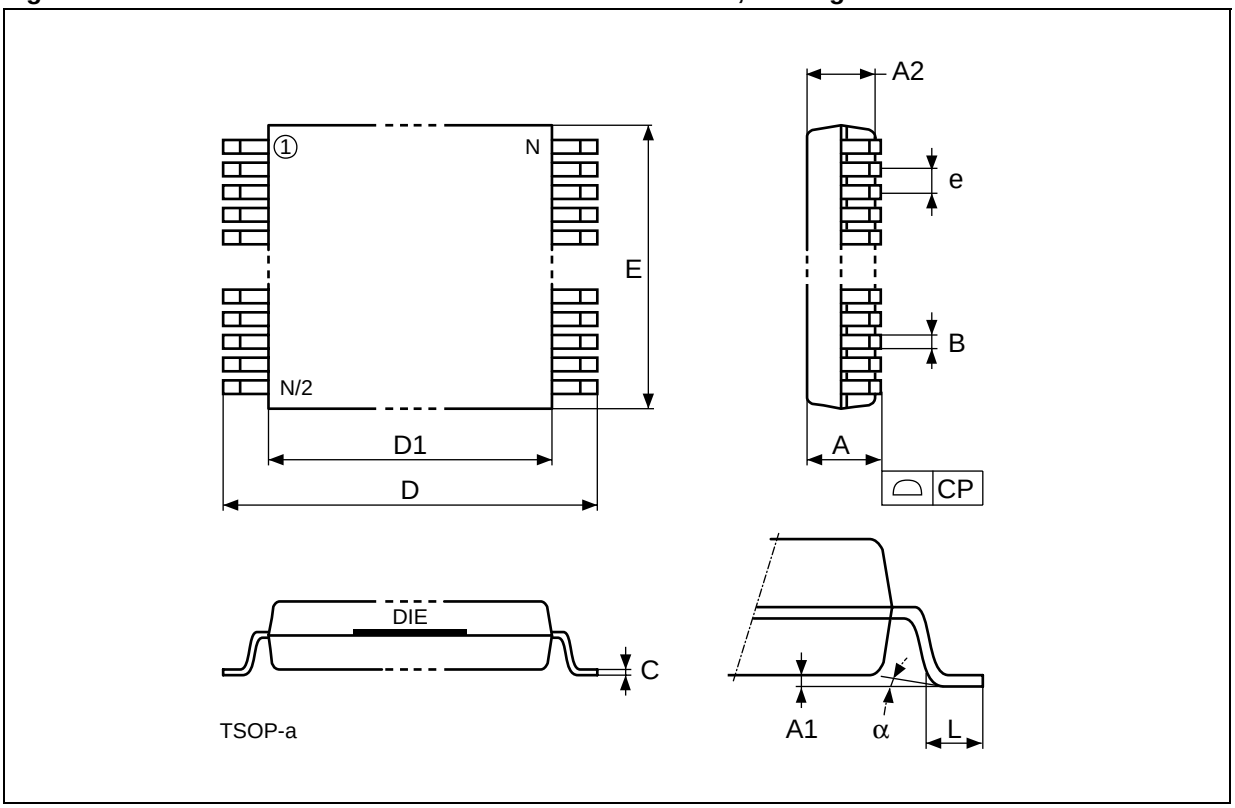


Note: Drawing is not to scale.

Table 10. SO32 - 32 lead Plastic Small Outline, Package Mechanical Data

Symbol	millimeters			inches		
	Typ	Min	Max	Typ	Min	Max
A			2.997			0.118
A1		0.102			0.004	
A2		2.565	2.819		0.101	0.111
b		0.356	0.508		0.014	0.020
c		0.152	0.305		0.006	0.012
D		20.142	20.752		0.793	0.817
E		11.176	11.430		0.440	0.450
E1		13.868	14.376		0.546	0.566
e	1.270	–	–	0.050	–	–
L		0.584	0.991		0.023	0.039
L1		1.194	1.600		0.047	0.063
CP			0.10			0.004

Figure 16. TSOP32 - 32 lead Plastic Small Outline 8x20mm, Package Outline

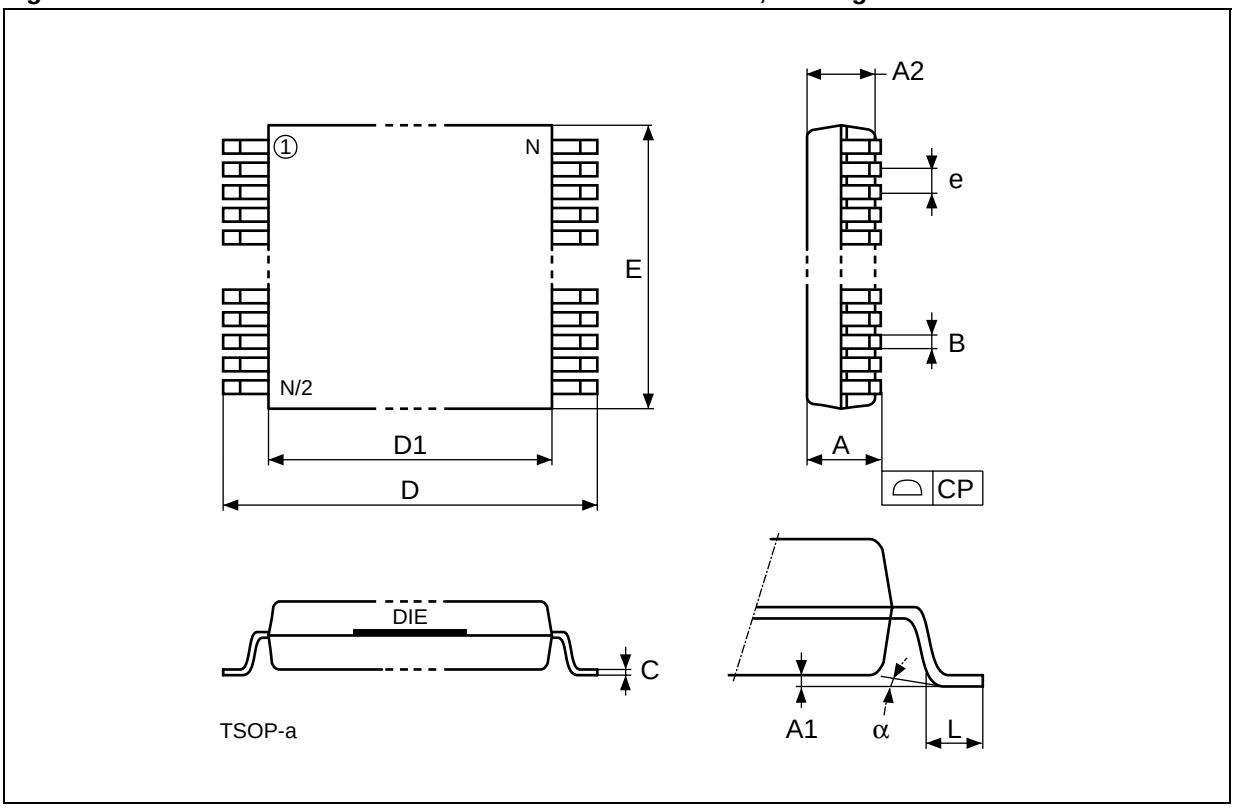


Note: Drawing is not to scale.

Table 11. TSOP32 - 32 lead Plastic Small Outline 8x20mm, Package Mechanical Data

Symbol	millimeters			inches		
	Typ	Min	Max	Typ	Min	Max
A			1.200			0.0472
A1		0.050	0.150		0.0020	0.0059
A2		0.950	1.050		0.0374	0.0413
B		0.170	0.250		0.0067	0.0098
C		0.100	0.210		0.0039	0.0083
CP			0.100			0.0039
D		19.800	20.200		0.7795	0.7953
D1		18.300	18.500		0.7205	0.7283
E		7.900	8.100		0.3110	0.3189
e	0.500	–	–	0.0197	–	–
L		0.500	0.700		0.0197	0.0276
α		0°	5°		0°	5°
N	32			32		

Figure 17. TSOP32 - 32 lead Plastic Small Outline 8x13.4mm, Package Outline



Note: Drawing is not to scale.

Table 12. TSOP32 - 32 lead Plastic Small Outline 8x13.4mm, Package Mechanical Data

Symbol	millimeters			inches		
	Typ	Min	Max	Typ	Min	Max
A			1.20			0.0472
A1		0.05	0.15		0.0020	0.0059
A2		0.91	1.05		0.0358	0.0413
B	0.22			0.0087		
C		0.10	0.21		0.0039	0.0083
D	13.40	–	–	0.5276	–	–
D1	11.80	–	–	0.4646	–	–
E	8.00	–	–	0.3150	–	–
e	0.50	–	–	0.0197	–	–
L		0.40	0.60		0.0157	0.0236
α		0	5		0	5
N	32			32		
CP			0.10			0.0039

PART NUMBERING

Table 13. Ordering Information Scheme

Example: M68AW127 B L 70 N 6T

Device Type
M68

Mode
A = Asynchronous

Operating Voltage
W = 2.7 to 3.6V

Array Organization
127 = 1Mbit (128K x8)

Option 1
B = 2 Chip Enable

Option 2
L = L-Die
M = M-Die

Speed Class
70 = 70ns
10 = 100ns

Package
MC = SO32
N = TSOP32 (8 x 20mm)
NK = TSOP32 (8 x 13.4mm)

Operative Temperature
1 = 0 to 70°C
6 = –40 to 85°C

Shipping
T = Tape & Reel Packing

For a list of available options (e.g., Speed, Package) or for further information on any aspect of this device, please contact the STMicroelectronics Sales Office nearest to you.

REVISION HISTORY

Table 14. Document Revision History

Date	Version	Revision Details
January 2002	1.0	First Issue
09-May-2002	2.0	DC Characteristics table clarified (Table 6) $\overline{E1}$ Controlled, Low V_{CC} Data Retention AC Waveforms clarified (Figure 13) Low V_{CC} Data Retention Characteristics table clarified (Table 9) Ordering Information Scheme clarified (Table 13)
01-Jul-2002	3.0	70ns speed class added SO32 and TSOP32 8x13.4mm package options added
11-Sep-2002	4.0	Commercial code clarified
02-Oct-2002	4.1	Title and header layout modified.
09-Oct-2002	4.2	Commercial code modified.
16-Apr-2003	4.3	Label corrected on “E2 Controlled, Low V_{CC} Data Retention AC Waveforms” figure
21-Aug-2003	4.4	TSOP Package connections modified (Figure 5)
24-Sep-2004	5	Document structure modified: – Chapter OPERATION moved before chapter MAXIMUM RATING. – AC Characteristics Tables and waveforms moved to the DC/AC PARAMETERS section. t_{PU} ad t_{PD} updated in Table 7.